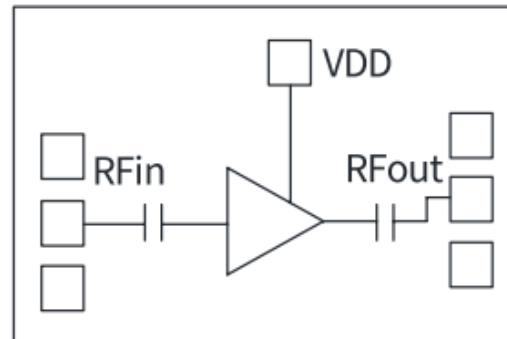


Features

- Single Biasing Voltage(Self Biased)
- Frequency: 20-31GHz
- Gain: 18dB
- P1dB: +17dBm
- Power supply: +5.0V@55mA
- Die Size: 1200 x 750 μm

Typical Applications

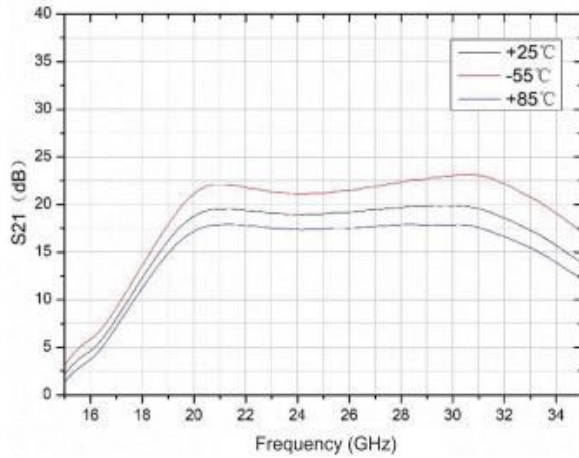
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Functional Block Diagram

Electrical Specifications

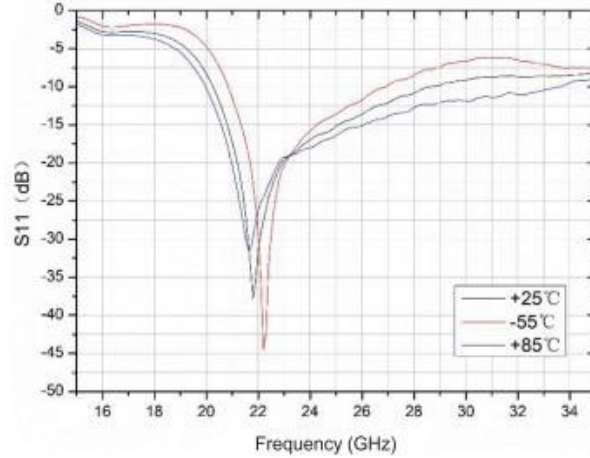
TA = +25°C, Vdd = +5V, self-biased

Parameters	Min.	Typ.	Max.	Units
Frequency	20-31			GHz
Gain		18		dB
Gain Flatness		± 1		dB
Reverse Isolation		35		dB
P1dB		17		dBm
Input Return Loss		12		dB
Output Return Loss		12		dB
Operating Current		55		mA

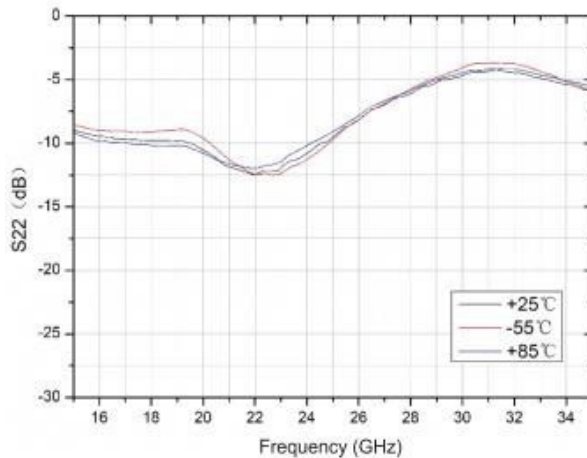
Gain vs. Frequency



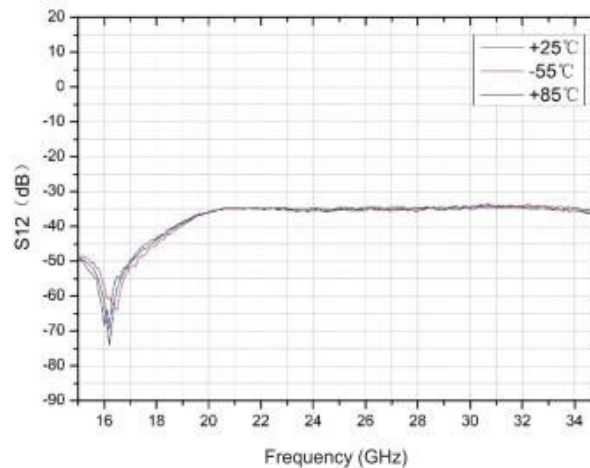
Input Return Loss vs. Frequency



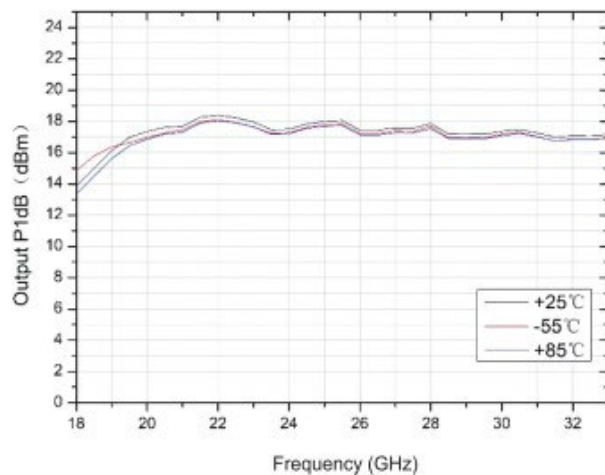
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

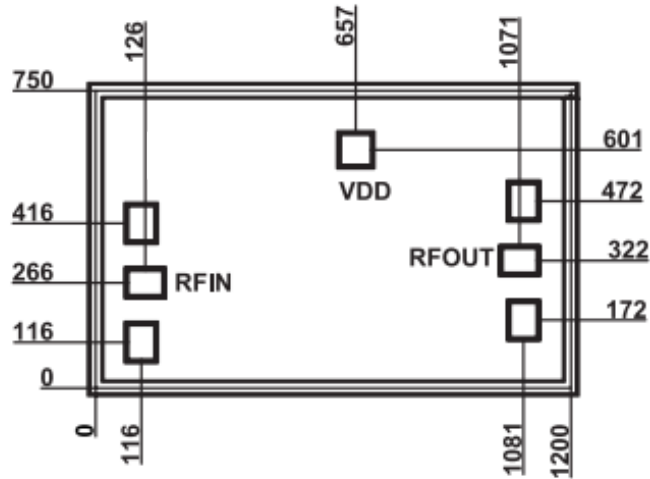


P-1dB vs. Frequency

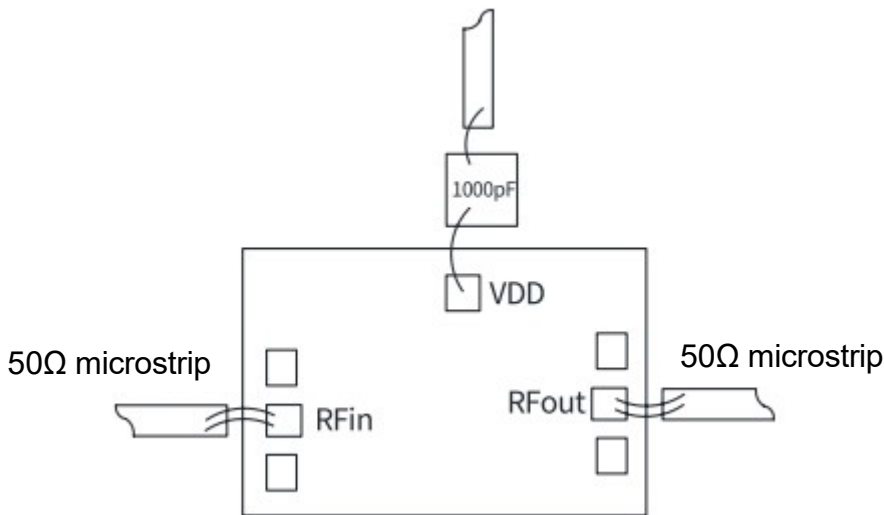




Outline Drawing: All Dimensions in um



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads